

$^{28}\text{Si}(\text{pol p,p}') E=6.4-7.7 \text{ keV}$  [1992Wi13](#)

Type	Author	History	Citation	Literature Cutoff Date
Full Evaluation	M. Shamsuzzoha Basunia		NDS 113, 909 (2012)	1-Jan-2012

Other: [1976Ik03](#).

$^{28}\text{SiO}$  target; Projectile: pol P, E=6.4 to 7.7 MeV; silicon surface-barrier detectors; deduced resonance level energies and parameters.

 $^{29}\text{P}$  Levels

E(level)	$J^\pi$ <sup>†</sup>	$T_{1/2}$	Comments
0			
8386 2	5/2 <sup>+</sup>	0.271 keV 10	$\Gamma_p=0.216 \text{ keV}$ 5
9664 2	1/2 <sup>+</sup>	3.07 keV 5	$\Gamma_p=2.43 \text{ keV}$ 4
10490 2	3/2 <sup>+</sup>	0.88 keV 17	$\Gamma_p=0.099 \text{ keV}$ 11
11360 2	5/2 <sup>+</sup>	3.5 keV 5	$\Gamma_p=0.11 \text{ keV}$ 2
11480 2	5/2 <sup>+</sup>	1.53 keV 12	$\Gamma_p=0.37 \text{ keV}$ 2

<sup>†</sup> Extracted in [1992Wi13](#) from (p,p') cross section data fitting.